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# PSMN022-30PL,127

**NXP Semiconductors** 

MOSFET PSMN022-30PL/SOT78/SIL3P

Any questions, please feel free to contact us. info@kaimte.com



# **PSMN022-30PL**

# N-channel 30 V 22 m $\Omega$ logic level MOSFET

Rev. 02 — 1 November 2010

Product data sheet

## 1. Product profile

## 1.1 General description

Logic level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

## 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

	44.01.10.010.100					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	30	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see Figure 1	-	-	30	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see Figure 2	-	-	41	W
Tj	junction temperature		-55	-	175	°C
Static cha	racteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{\text{ Figure } 13}$	-	27	34	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{\text{Figure } 13}$	-	19	22	mΩ
Dynamic o	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A};$	-	1.4	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.4	-	nC
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} &V_{GS} = 10 \text{ V; } T_{j(\text{init})} = 25 \text{ °C;} \\ &I_D = 30 \text{ A; } V_{\text{sup}} \leq 30 \text{ V;} \\ &R_{GS} = 50  \Omega; \text{ unclamped} \end{split}$	-	-	7	mJ



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN022-30PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78		

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

$ \begin{array}{ c c c c c } \hline \textbf{Symbol} & \textbf{Parameter} & \textbf{Conditions} & \textbf{Min} & \textbf{Max} & \textbf{Unit} \\ \hline V_{DS} & drain-source voltage & T_j \geq 25  ^{\circ}\text{C}; T_j \leq 175  ^{\circ}\text{C} & - & 30 & V \\ \hline V_{DGR} & drain-gate voltage & T_j \geq 25  ^{\circ}\text{C}; T_j \leq 175  ^{\circ}\text{C}; R_{GS} = 20  k\Omega & - & 30 & V \\ \hline V_{GS} & gate-source voltage & -20 & 20 & V \\ \hline I_D & drain current & V_{GS} = 10  V; T_{mb} = 100  ^{\circ}\text{C}; see Figure 1 & - & 22 & A \\ \hline V_{GS} = 10  V; T_{mb} = 25  ^{\circ}\text{C}; see Figure 1 & - & 30 & A \\ \hline I_{DM} & peak drain current & pulsed; t_p \leq 10  \mu s; T_{mb} = 25  ^{\circ}\text{C}; see Figure 3 & - & 125 & A \\ \hline P_{tot} & total power dissipation & T_{mb} = 25  ^{\circ}\text{C}; see Figure 2 & - & 41 & W \\ \hline T_{stg} & storage temperature & -55 & 175 & ^{\circ}\text{C} \\ \hline T_j & junction temperature & -55 & 175 & ^{\circ}\text{C} \\ \hline Source-drain diode & & & & & \\ \hline I_S & source current & T_{mb} = 25  ^{\circ}\text{C} & - & 30 & A \\ \hline I_{SM} & peak source current & pulsed; t_p \leq 10  \mu s; T_{mb} = 25  ^{\circ}\text{C} & - & 125 & A \\ \hline \textbf{Avalanche ruggedness} & & & & & \\ \hline E_{DS(AL)S} & & & & & & & \\ \hline non-repetitive drain-source & V_{GS} = 10  V; T_{j(init)} = 25  ^{\circ}\text{C}; I_D = 30  A; & - & 7 & mJ \\ \hline \end{array}$			,			
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Symbol	Parameter	Conditions	Min	Max	Unit
$\begin{array}{c} V_{GS} & \text{gate-source voltage} \\ I_D & \text{drain current} \\ \hline \\ V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \underline{Figure 1} \\ \hline \\ V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \underline{Figure 1} \\ \hline \\ V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \underline{Figure 1} \\ \hline \\ V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \underline{Figure 3} \\ \hline \\ P_{tot} & \text{total power dissipation} \\ \hline \\ T_{stg} & \text{storage temperature} \\ \hline \\ T_{j} & \text{junction temperature} \\ \hline \\ S_{j} & \text{source current} \\ \hline \\ I_{S} & \text{source current} \\ \hline \\ I_{SM} & \text{peak source current} \\ \hline \\ P_{ulsed}; t_{p} \leq 10  \mu \text{s}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; t_{p} \leq 10  \mu \text{s}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; t_{p} \leq 10  \mu \text{s}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C}; T_{mb} = 25 \text{ °C} \\ \hline \\ P_{ulsed}; T_{mb} = 25 \text{ °C}; T_{mb} = 25 \text{ °C}$	$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	30	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$V_{DGR}$	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
$V_{GS} = 10 \text{ V; } T_{mb} = 25 \text{ °C; see } \underline{Figure 1} \qquad - \qquad 30 \qquad A$ $I_{DM} \qquad \text{peak drain current} \qquad \text{pulsed; } t_p \leq 10  \mu \text{s; } T_{mb} = 25 \text{ °C; see } \underline{Figure 3} \qquad - \qquad 125  A$ $P_{tot} \qquad \text{total power dissipation} \qquad T_{mb} = 25 \text{ °C; see } \underline{Figure 2} \qquad - \qquad 41  W$ $T_{stg} \qquad \text{storage temperature} \qquad \qquad -55  175  \text{°C}$ $T_j \qquad \text{junction temperature} \qquad \qquad -55  175  \text{°C}$ $Source-drain \ diode$ $I_S \qquad \text{source current} \qquad T_{mb} = 25 \text{ °C} \qquad - \qquad 30  A$ $I_{SM} \qquad \text{peak source current} \qquad \text{pulsed; } t_p \leq 10  \mu \text{s; } T_{mb} = 25 \text{ °C} \qquad - \qquad 125  A$ $Avalanche \ ruggedness$ $E_{DS(AL)S} \qquad \text{non-repetitive drain-source} \qquad V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C; } I_D = 30 \text{ A;} \qquad - \qquad 7  \text{mJ}$	$V_{GS}$	gate-source voltage		-20	20	V
IDMpeak drain currentpulsed; $t_p ≤ 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C;$ see Figure 3-125APtottotal power dissipation $T_{mb} = 25 \ ^{\circ}C;$ see Figure 2-41W $T_{stg}$ storage temperature-55175 $^{\circ}C$ $T_j$ junction temperature-55175 $^{\circ}C$ Source-drain diode $I_S$ source current $T_{mb} = 25 \ ^{\circ}C$ -30A $I_{SM}$ peak source currentpulsed; $t_p ≤ 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C$ -125AAvalanche ruggedness $E_{DS(AL)S}$ non-repetitive drain-source $V_{GS} = 10 \ V; T_{j(init)} = 25 \ ^{\circ}C; I_D = 30 \ A;$ -7mJ	$I_D$	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	22	Α
$\begin{array}{cccccccccccccccccccccccccccccccccccc$			$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \underline{\text{Figure 1}}$	-	30	Α
T <sub>stg</sub> storage temperature -55 175 °C  T <sub>j</sub> junction temperature -55 175 °C  Source-drain diode  I <sub>S</sub> source current $T_{mb} = 25$ °C - 30 A  I <sub>SM</sub> peak source current pulsed; $t_p \le 10$ µs; $T_{mb} = 25$ °C - 125 A  Avalanche ruggedness  E <sub>DS(AL)S</sub> non-repetitive drain-source $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $I_D = 30$ A; - 7 mJ	I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	125	Α
$T_{j} \qquad \text{junction temperature} \qquad \qquad -55 \qquad 175  ^{\circ}\text{C}$ $ \begin{array}{ccccccccccccccccccccccccccccccccccc$	P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	41	W
Source-drain diode	T <sub>stg</sub>	storage temperature		-55	175	°C
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Tj	junction temperature		-55	175	°C
I <sub>SM</sub> peak source current pulsed; $t_p ≤ 10 \mu s$ ; $T_{mb} = 25 °C$ - 125 A <b>Avalanche ruggedness</b> E <sub>DS(AL)S</sub> non-repetitive drain-source $V_{GS} = 10 V$ ; $T_{j(init)} = 25 °C$ ; $I_D = 30 A$ ; - 7 mJ	Source-drain	diode				
Avalanche ruggedness $E_{DS(AL)S} \qquad \text{non-repetitive drain-source} \qquad V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C; } I_D = 30 \text{ A;} \qquad \qquad 7 \qquad \text{mJ}$	Is	source current	T <sub>mb</sub> = 25 °C	-	30	Α
$E_{DS(AL)S}$ non-repetitive drain-source $V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; I_D = 30 \text{ A};$ - 7 mJ	I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	125	Α
DO(/\L)O	Avalanche ru	ggedness				
	E <sub>DS(AL)S</sub>	•		-	7	mJ

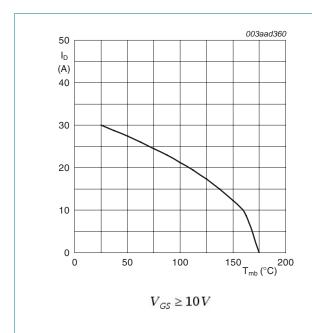


Fig 1. Continuous drain current as a function of mounting base temperature

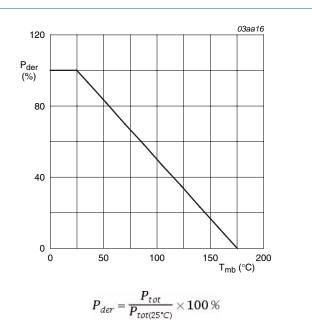


Fig 2. Normalized total power dissipation as a function of mounting base temperature

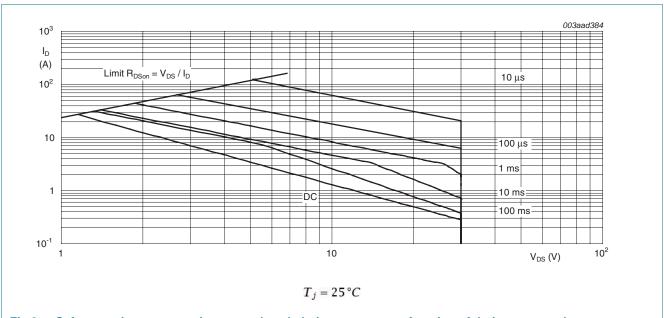


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	3.1	3.6	K/W

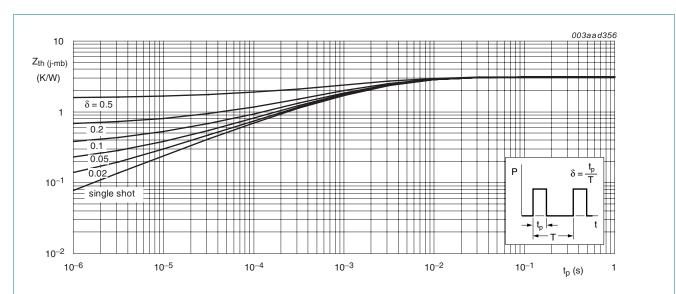


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

# 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.3	1.7	2.15	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; see <u>Figure 11</u>	0.5	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; see <u>Figure 11</u>	-	-	2.45	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	50	μΑ
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see <u>Figure 12</u>	-	-	64.6	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 13</u>	-	27	34	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 175 °C;$ see <u>Figure 12</u>	-	35	41.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 100 °C;$ see <u>Figure 12</u>	-	-	31	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 13</u>	-	19	22	mΩ
$R_G$	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 5 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15	-	9	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	8	-	nC
		$I_D = 5 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ;	-	4.4	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 14; see Figure 15	-	1.6	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 5 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; see Figure 14	-	8.0	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	8.0	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 5 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	1.4	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V <sub>DS</sub> = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	3	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	447	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	96	-	pF

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 1.5 \Omega; V_{GS} = 4.5 \text{ V};$ $R_{G(ext)} = 4.7 \Omega$	-	12	-	ns
t <sub>r</sub>	rise time		-	29	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	17	-	ns
t <sub>f</sub>	fall time		-	7	-	ns
Source-dra	in diode					
$V_{SD}$	source-drain voltage	$I_S = 5 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	0.7	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 5 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ;	-	22	-	ns
Qr	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$	-	10	-	nC

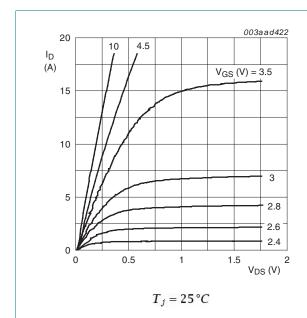


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

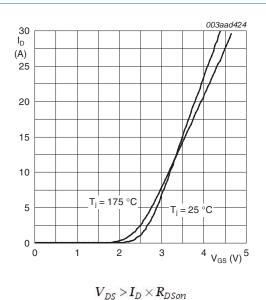


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

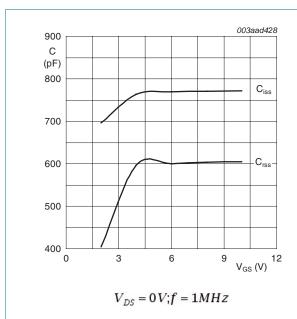


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

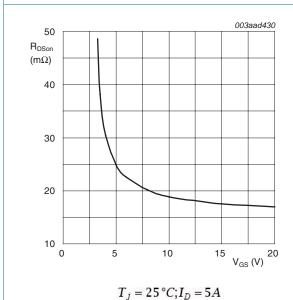
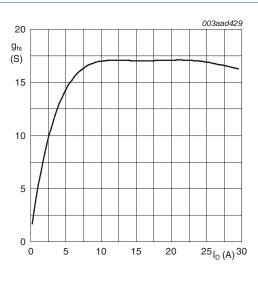
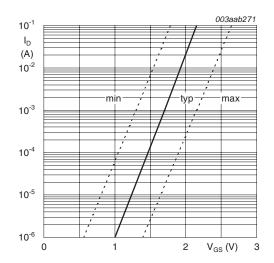


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_j = 25 \,{}^{\circ}C; V_{DS} = 10 \, V$ 

Fig 8. Forward transconductance as a function of drain current; typical values



$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

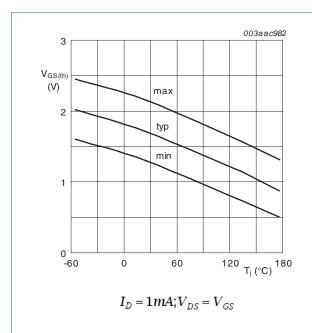


Fig 11. Gate-source threshold voltage as a function of junction temperature

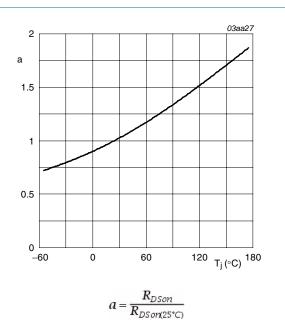


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

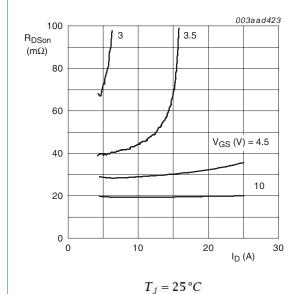


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

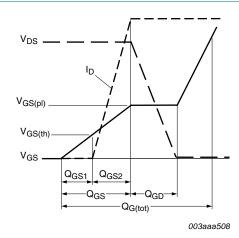


Fig 14. Gate charge waveform definitions

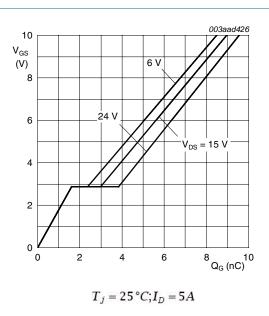
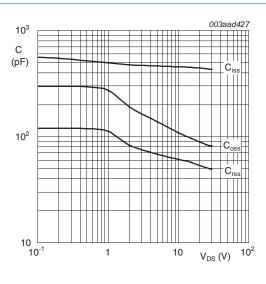


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

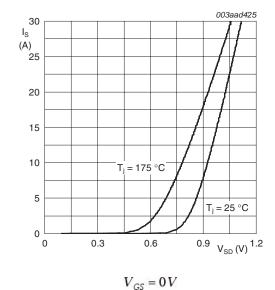
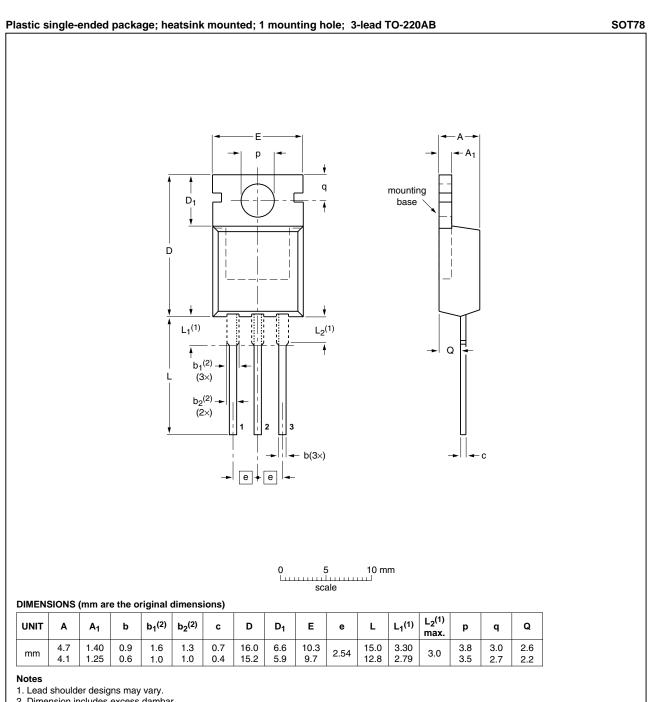


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

# Package outline



2. Dimension includes excess dambar.

OUTLINE REFERENCES		ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13

Fig 18. Package outline SOT78 (TO-220AB)

PSMN022-30PL

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# 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN022-30PL v.2	20101101	Product data sheet	-	PSMN022-30PL v.1
Modifications:	<ul> <li>Various change</li> </ul>	es to content.		
PSMN022-30PL v.1	20101018	Product data sheet	-	-

## 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

#### 9.2 Definitions

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## 10. Contact information

For more information, please visit: http://www.nexperia.com

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# **PSMN022-30PL**

# **Nexperia**

N-channel 30 V 22 mΩ logic level MOSFET

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